Abstract

Method for polishing a semiconductor wafer

A method for polishing a semiconductor wafer by means of a polishing pad which comprises fixedly bonded abrasives of SiO_2 having an average grain size of 0.1 to 1.0 µm, and with supply of an aqueous polishing agent solution which comprises an alkaline component, is free of solid materials and has a variable pH value of 11 to 13.5, wherein the polishing agent solution has a pH value of less than 13 during the polishing process, said pH value being increased to 13 to 13.5 for the purpose of ending the polishing process.